

ABSTRACT

5       An object of the present invention is to provide a  
method of producing a Group III nitride semiconductor  
device having a chip form which is pentagonal or more  
highly polygonal maintaining good area efficiency and at  
a low cost.

10       The inventive method of producing a Group III  
nitride semiconductor device having a chip shape which is  
a pentagonal or more highly polygonal shape comprises a  
first step of epitaxially growing a Group III nitride  
semiconductor on a substrate to form a semiconductor  
wafer; a second step of irradiating said semiconductor  
wafer with a laser beam to form separation grooves; a  
15   third step of grinding and/or polishing the main surface  
side differently from the epitaxially grown main surface  
of the substrate; and a fourth step of division into  
individual chips by applying stress to said separation  
grooves.